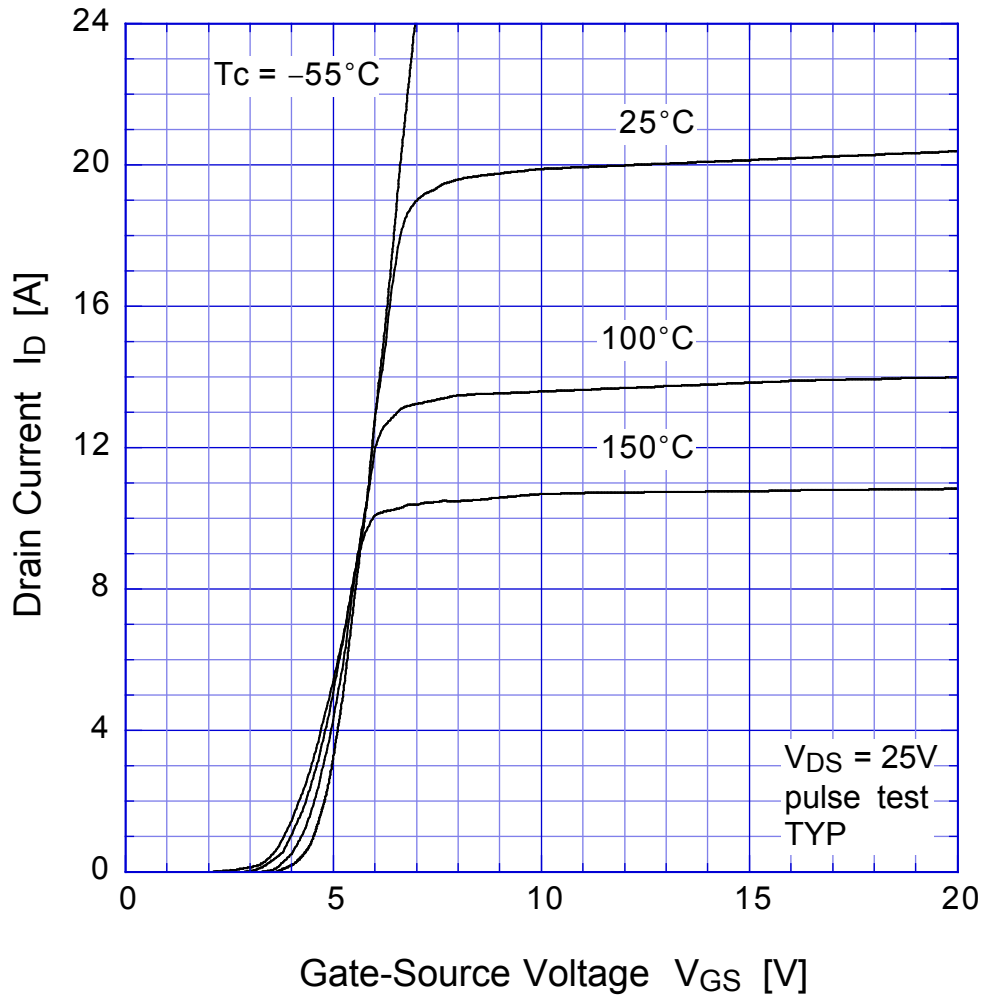


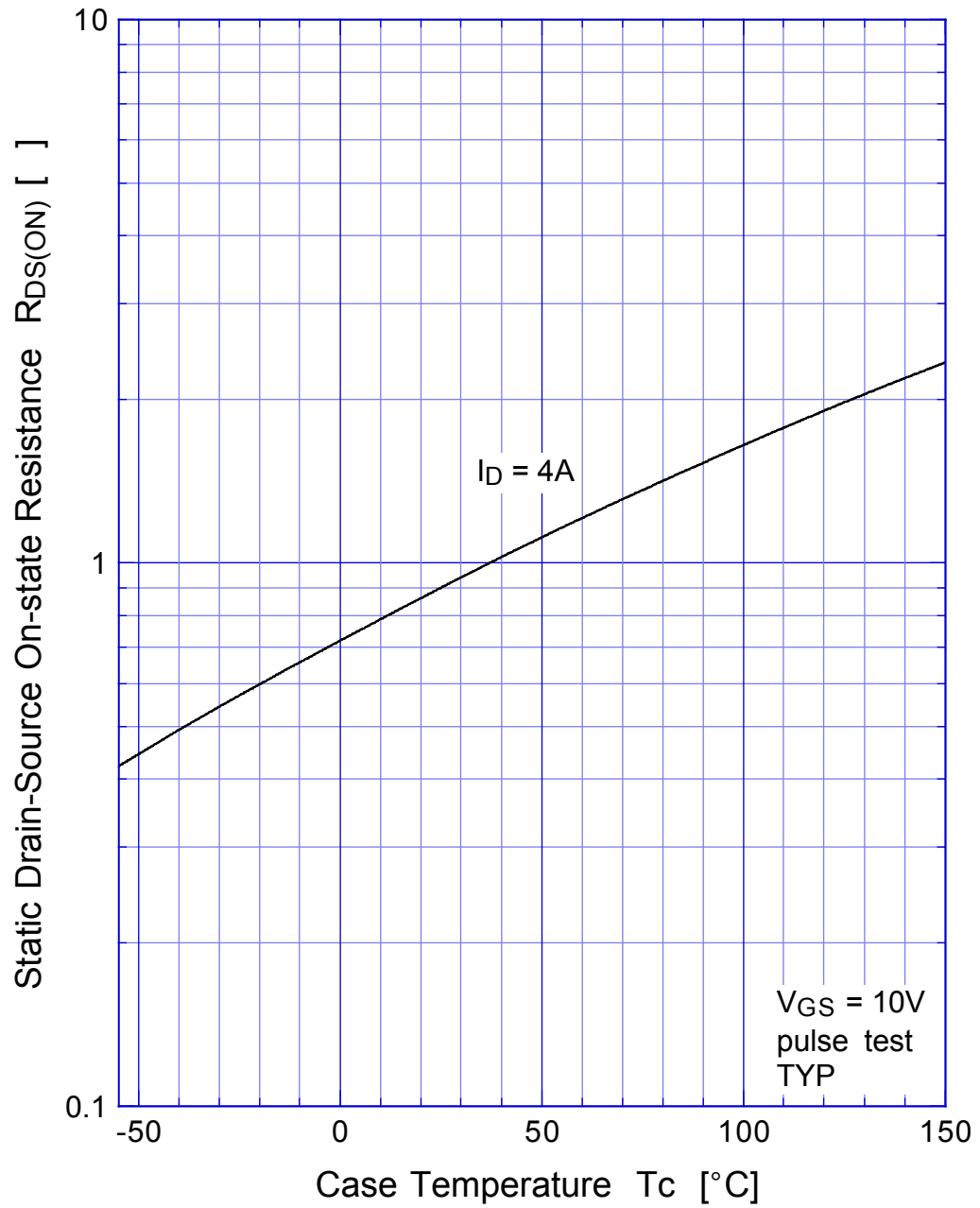
●Electrical Characteristics $T_c = 25^\circ\text{C}$

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$			250	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 0.1	
Forward Transconductance	g_{fs}	$I_D = 4\text{A}, V_{DS} = 10\text{V}$	2.4	5.5		S
Static Drain-Source On-state Resistance	$R_{DS(ON)}$	$I_D = 4\text{A}, V_{GS} = 10\text{V}$		0.9	1.2	Ω
Gate Threshold Voltage	V_{TH}	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$	2.5	3.0	3.5	V
Source-Drain Diode Forwade Voltage	V_{SD}	$I_S = 4\text{A}, V_{GS} = 0\text{V}$			1.5	
Thermal Resistance	θ_{jc}	junction to case			2.5	$^\circ\text{C}/\text{W}$
Total Gate Charge	Q_g	$V_{DD} = 400\text{V}, V_{GS} = 10\text{V}, I_D = 8\text{A}$		42		nC
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1130		pF
Reverse Transfer Capacitance	C_{rss}			85		
Output Capacitance	C_{oss}			245		
Turn-On Time	t_{on}	$I_D = 4\text{A}, R_L = 37.5\Omega, V_{GS} = 10\text{V}$		55	80	ns
Turn-Off Time	t_{off}			195	290	

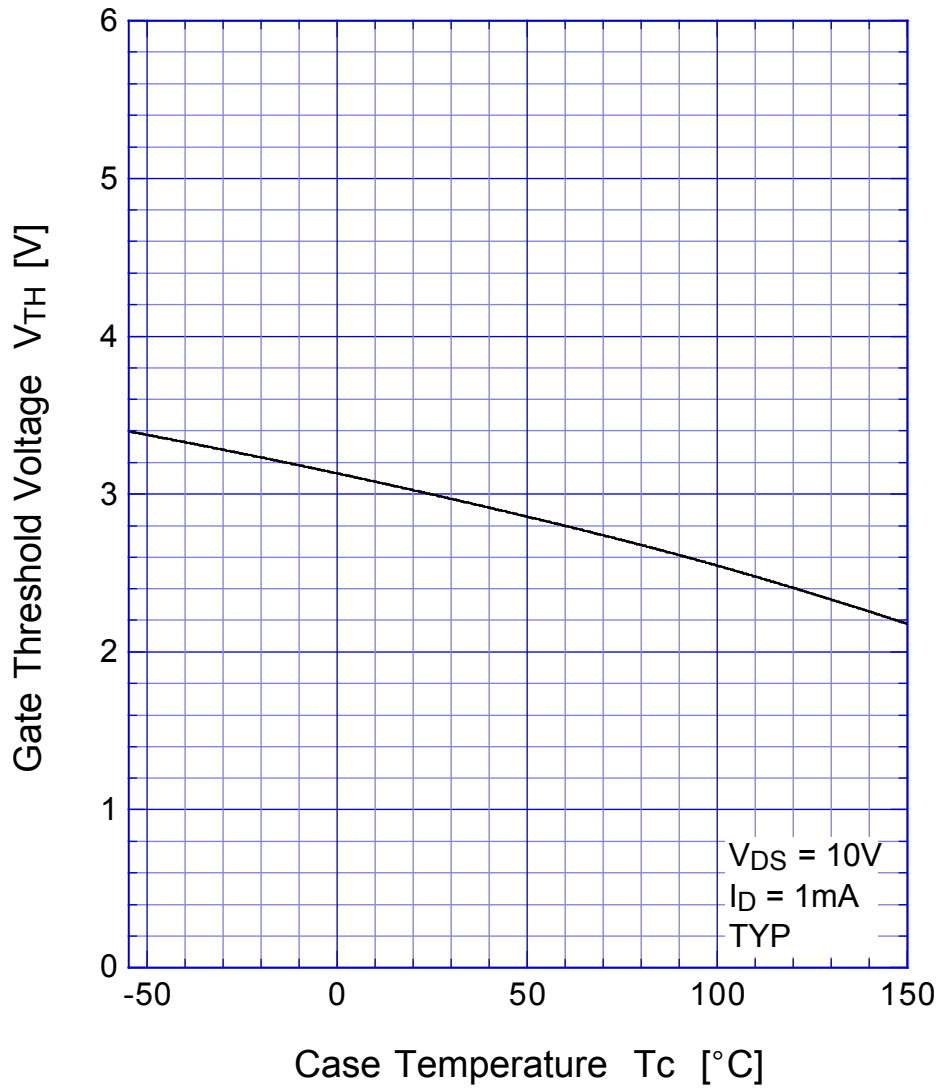
2SK2564 Transfer Characteristics



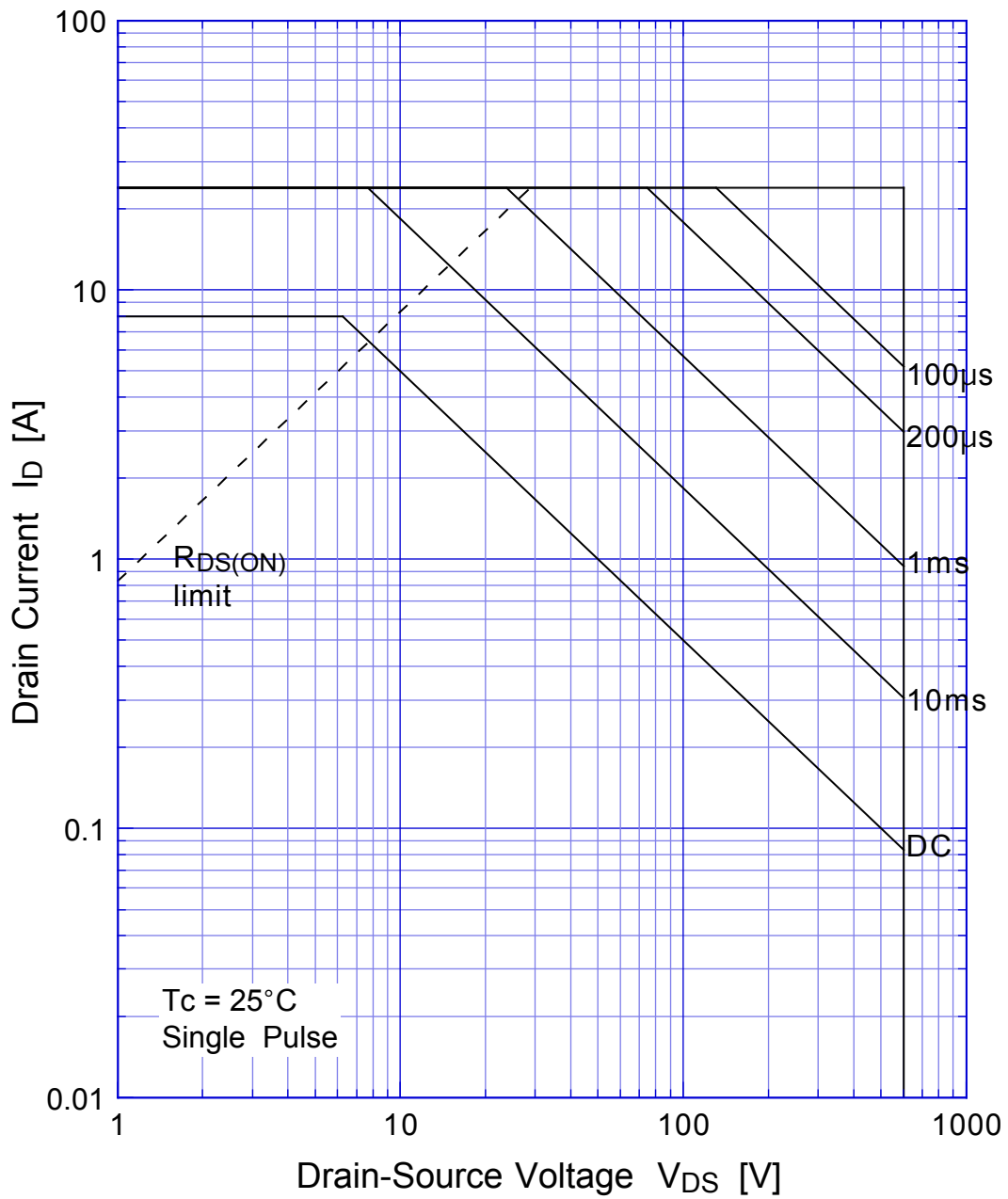
2SK2564 Static Drain-Source On-state Resistance



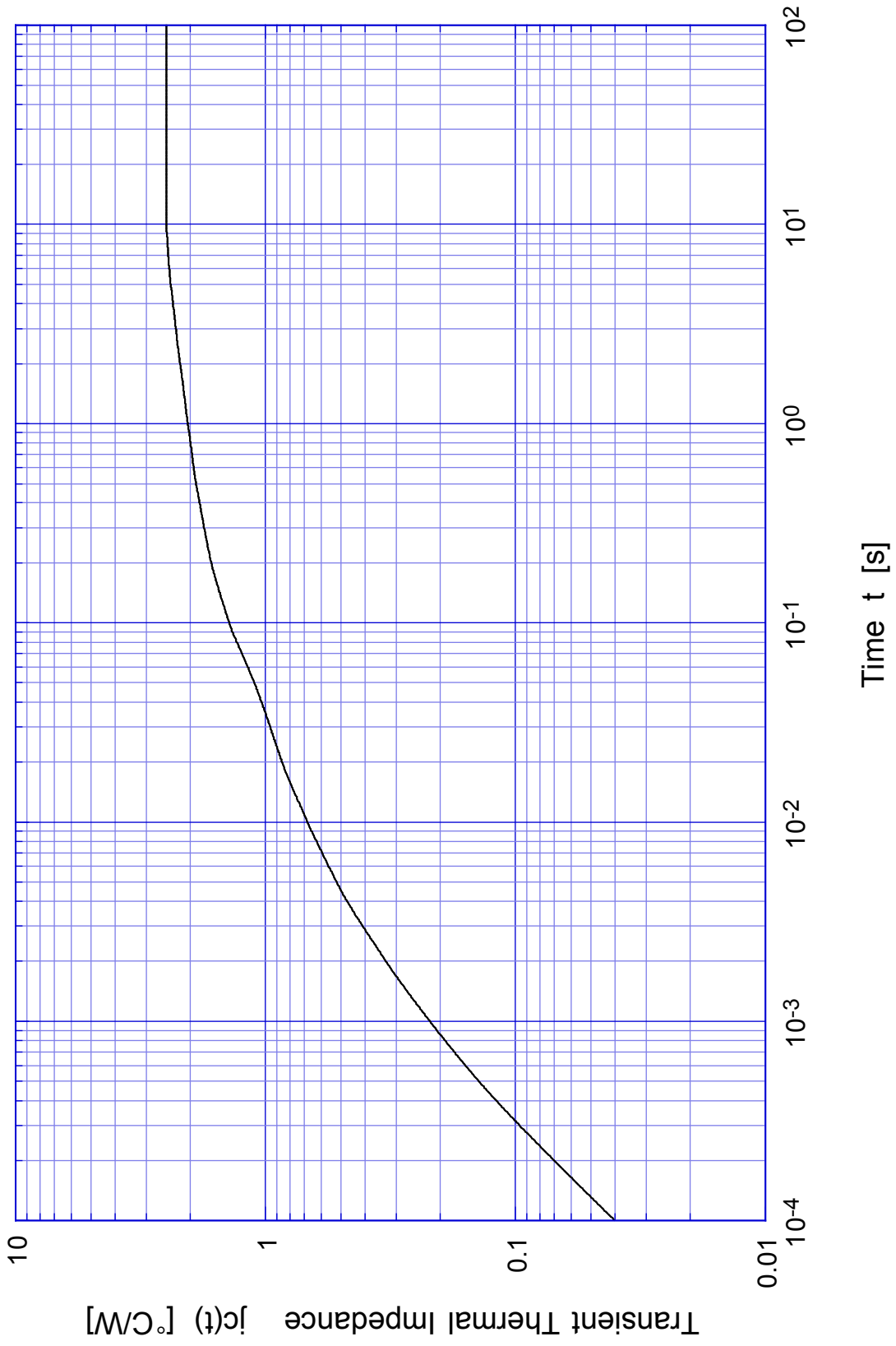
2SK2564 Gate Threshold Voltage



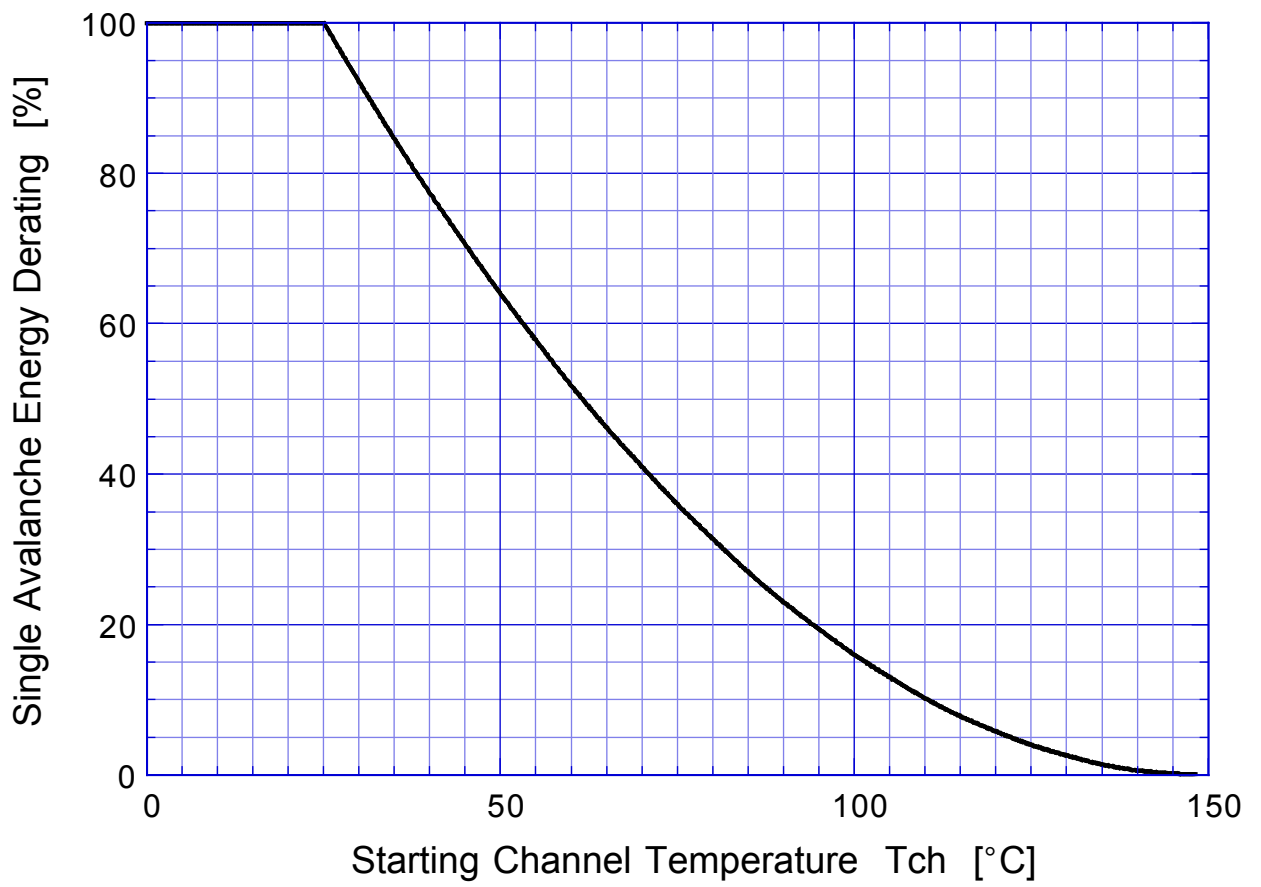
2SK2564 Safe Operating Area



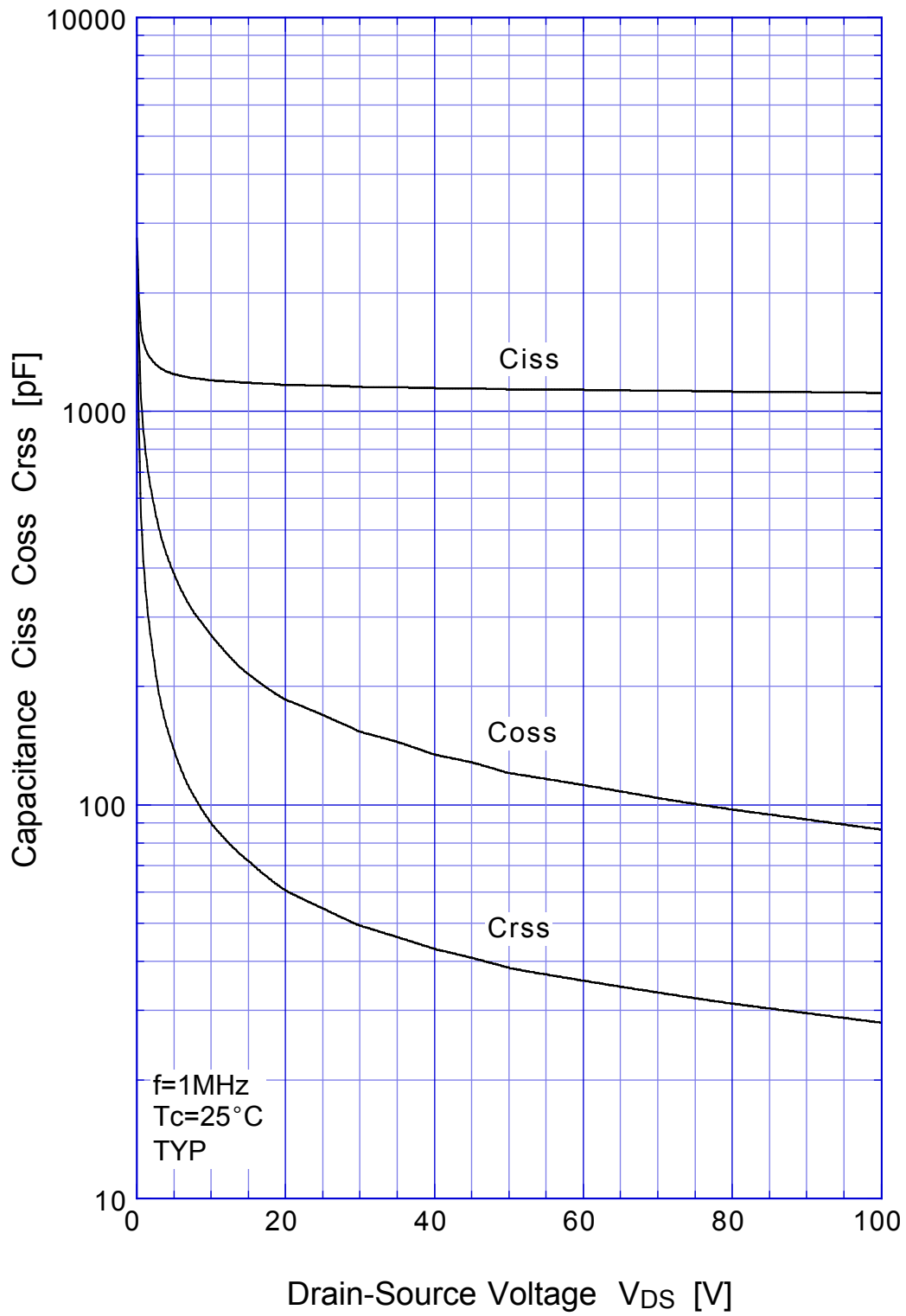
2SK2564 Transient Thermal Impedance



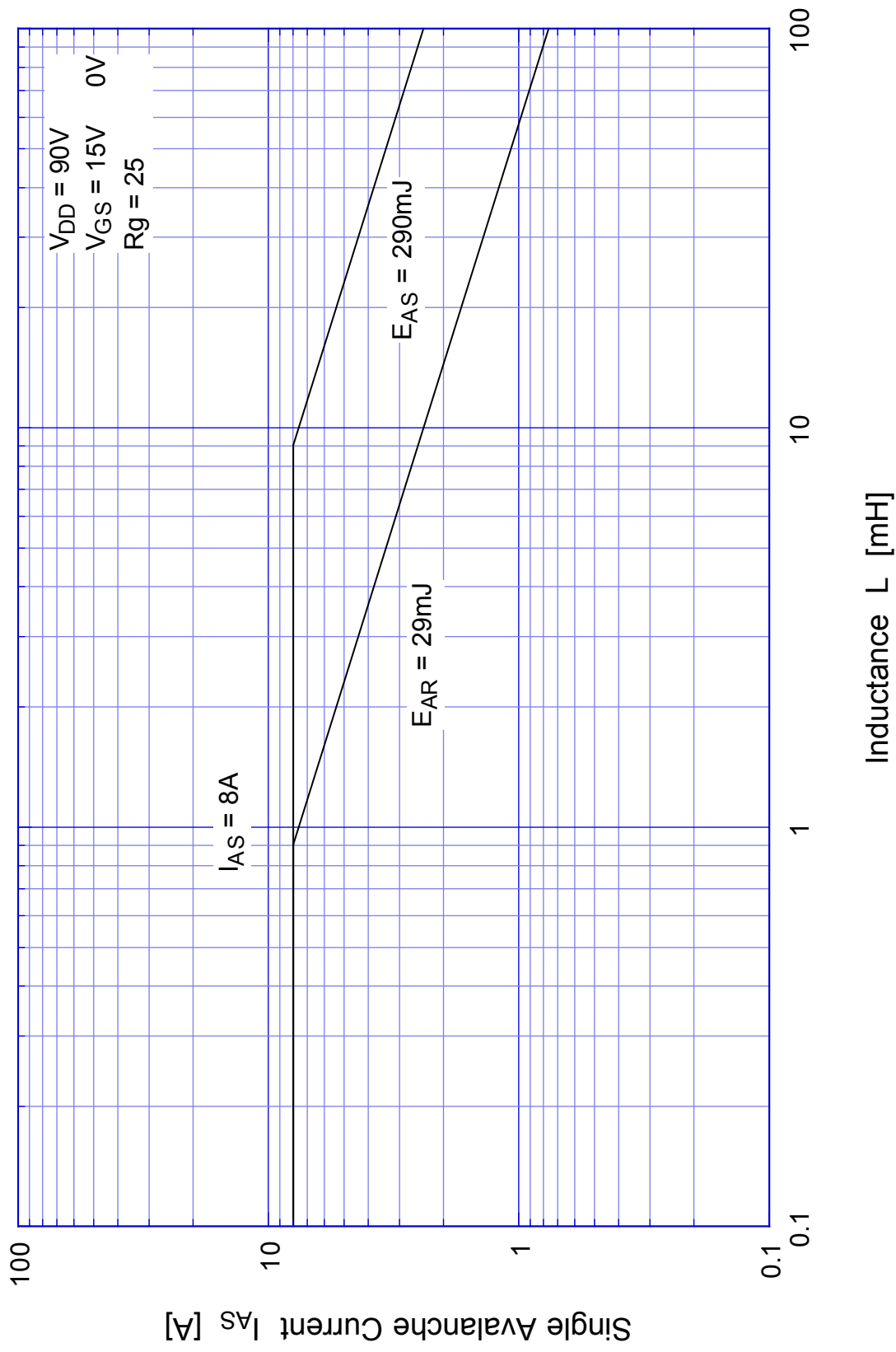
2SK2564 Single Avalanche Energy Derating



2SK2564 Capacitance

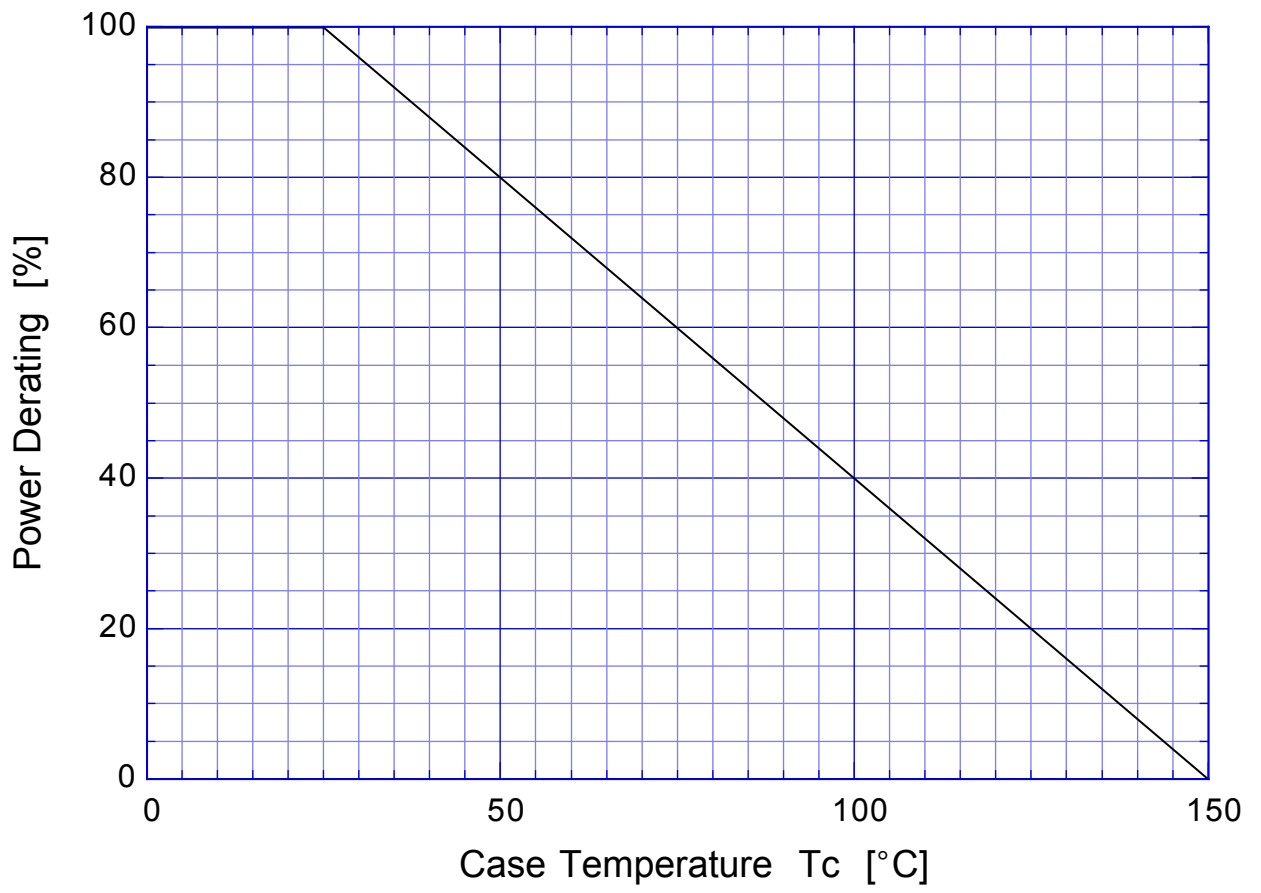


2SK2564 Single Avalanche Current - Inductive Load



2SK2564

Power Derating



2SK2564 Gate Charge Characteristics

